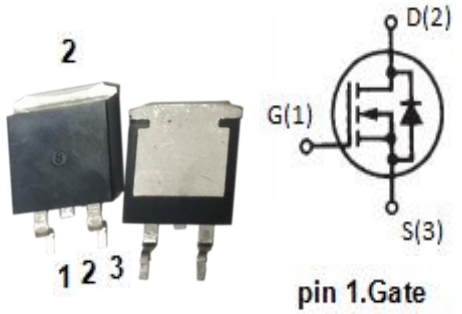
isc N-Channel MOSFET Transistor FDD6672A

FEATURES

- Drain Current : I_D=65A@ T_C=25℃
- Drain Source Voltage
  : V_{DSS}=30V(Min)
- Static Drain-Source On-Resistance
  : $R_{DS(on)}$ =8mΩ(Max) @ V_{GS}= 10V
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



D²PAK

pin 1.Gate
2.Drain
3.Source
TO-263 package

DESCRIPTION

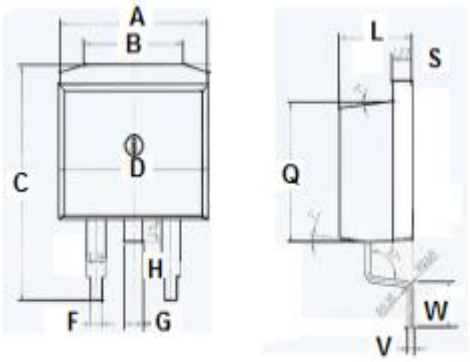
- motor drive, DC-DC converter, power switch and solenoid drive.

• ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	30	V
V_{GSS}	Gate-Source Voltage	±12	V
I_D	Drain Current-Continuous;@Tc=25℃	65	A
I_{DM}	Drain Current-Single Pulsed	100	A
P_D	Total Dissipation	70	W
T_j	Operating Junction Temperature	-55~150	℃
T_{stg}	Storage Temperature	-55~150	℃

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
Rth(ch-c)	Channel-to-case thermal resistance	1.8	℃/W



DIM	mm	
	MIN	MAX
A	9.8	10.2
B	6.6	6.8
C	15.1	15.3
D	9.6	10
F	0.7	0.9
G	1.26	1.3
H	1.2	1.45
L	4.4	4.6
Q	9.2	9.3
S	1.25	1.35
V	0.4	0.6
W	2.6	2.8

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V; I_D= 0.25mA	30	-	-	V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}; I_D= 0.25mA	0.8	-	2.0	V
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}=10V; I_D=14A	-	-	8	mΩ
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±12V;V_{DS}= 0V	-	-	±100	nA
I_{DSS}	Drain-Source Leakage Current	V_{DS}=24V; V_{GS}= 0V	-	-	1	uA
V_{SD}	Diode forward voltage	I_{SD}=2.7A, V_{GS} = 0 V	-	-	1.2	V